



12-19-01

2811

EXPRESS MAIL NO. EV035490605US
Attorney Docket No. FUJ 00-01013RAM
Client/Matter No. 80458.0007

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Glen Fox, Fan Chu, Brian Eastep, Tomohiro Takamatsu, Ko Nakamura, and Yoshimasa Horii

Group Art Unit: 2811

Serial No. 09/742,204

Examiner:

Filed: December 20, 2000

For: PROCESS FOR PRODUCING HIGH QUALITY PZT FILMS FOR FERROELECTRIC MEMORY INTEGRATED CIRCUITS

CERTIFICATE OF MAILING BY EXPRESS MAIL

Assistant Commissioner for Patents
Washington, D.C. 20231

12-19-01
2811
HOGAN & HARTSON
PETER J. MEZA

Sir:

- The undersigned hereby certifies that the following documents:
1. Preliminary Amendment;
 2. Certificate of Mailing by Express Mail; and
 3. Return Postcard

relating to the above application, were deposited as "Express Mail", Mailing Label No. EV035490605US with the United States Postal Service, addressed to The Assistant Commissioner for Patents, Washington, D.C., 20231, on 11 December 2001

11 December 2001
Date

12/10/01
Date

Mailer

Peter J. Meza, Reg. No. 32,920
HOGAN & HARTSON LLP
One Tabor Center
1200 17th Street, Suite 1500
Denver, Colorado 80202
(719) 448-5906 Tel
(303) 899-7333 Fax



Atty. Docket No. FUJ 00-01013RAM
Client Matter No. 80458.0007
Express Mail Label No. EV035490605US

#71A
SELL
1-3-02

In re Application of:

Glen Fox, Fan Chu, Brian Eastep, Tomohiro Takamatsu,
Ko Nakamura, and Yoshimasa Horii

Serial No. 09/742,204

Filed: December 20, 2000

For: PROCESS FOR PRODUCING HIGH QUALITY PZT
FILMS FOR FERROELECTRIC MEMORY INTEGRATED
CIRCUITS

Examiner:

Art Unit: 2811

PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Please amend the above-identified patent application as follows:

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 7, line 1, with the following:

Figure 3 is a process flowchart illustrating an alternative process wherein
the top electrode layer is deposited following a first RTA anneal, and a second
RTA anneal is performed after etching of the PZT;

Please replace the paragraph beginning at page 7, line 5, with the following:

Figure 4 is a process flowchart illustrating an alternative process wherein
the top electrode layer is deposited following a first RTA anneal, and a second
RTA anneal is performed after etching of the PZT and deposition of an
encapsulation layer; and